

Claim Amendment

1-4. (canceled)

5. (canceled)

6. (canceled)

7. (currently amended) A structure of claim 17, wherein the structure includes multiple emitters formed in the n-well and located outside at least part of the drain contact region.
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8-10. (withdrawn)

11. (currently amended) A high holding voltage LVTSCR-like structure, comprising an emitter formed in an n-well,
a gate,
a drain contact region formed in the n-well and split into at least one first drain portion and at least one second drain portion, and
a floating drain, wherein the emitter is located so that at least part of the first drain portion of the drain contact region is located between the a gate and the emitter,
and at least the second drain portion is located on the other side of the emitter.

12. (canceled)

13. (canceled)

14. (original) A structure of claim 11, wherein the emitter comprises a plurality of emitter regions.

15. (canceled)

16. (previously presented) A structure of claim 11 +2, wherein the floating drain and drain contact region are separated by a shallow trench isolation region.17. (currently amended) A LVTSCR-like ESD protection structure, comprising a drain contact region formed in at least two parts in an n-well,
a p+ emitter formed in the n-well, and
a gate, wherein at least part of the drain contact region is located between the p+ emitter and the gate and part of the drain contact region is formed on the other side of the emitter.

18. (previously presented) A structure of claim 17, further comprising a floating drain located between the gate and the p+ emitter.